Transistor, NPN TO-3





Description:

High voltage power transistor.

Designed for use in high-voltage, high-speed, power switching in inductive circuit, motor control, solenoid and relay drivers.

Features:

- Collector-emitter sustaining voltage $V_{CEO\,(sus)}$ = 4,000V (Min.) Low collector-emitter saturation voltage $V_{CE\,(sat)}$ = 3V (Max.) at I_{C} = 8A, I_{B} = 2.5A

Maximum Ratings

Characteristic	Symbol	BUX80	Unit	
Collector-Emitter Voltage	V _{CEO}	400		
Collector-Emitter Voltage (V _{BE} = 0)	V _{CES}	800 V		
Emitter-Base Voltage	V _{EBO}	10		
Collector Current - Continuous -Peak	I _C	10 15	А	
Base Current-Continuous	I _B	5		
Total Power Dissipation at T _C = 25°C Derate above 25°C	P _D	100 0.8	W W/°C	
Operating and Storage Junction Temperature Range	T _J , T _{STG}	-65 to +200	°C	

Thermal Characteristics

Characteristics	Symbol	Max.	Unit
Thermal Resistance Junction to Case	$R_{\theta JC}$	1.25	°C/W

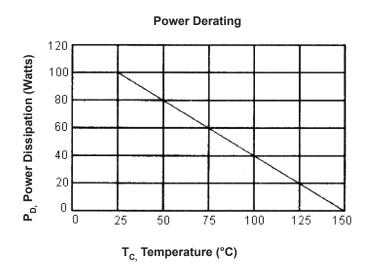
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17/09/19 V1.0

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Electrical Characteristics (TC = 25°C unless otherwise noted)

Ch	naracteristic	Symbol	Min.	Max.	Unit
Off Characteristics		•	•		•
Collector-Emitter Sustainin ($I_C = 100$ mA, $I_B = 0$, $L = 25$		V	400	-	V
Collector Cut off Current $(V_{CE} = 800V, V_{BE} = 0)$ $(V_{CE} = 800V, V_{BE} = 0, T_{C} = 125^{\circ}C)$		I _{CES}	-	1 3	mA
Emitter Cut off Current (V _{EB} = 10V, I _C = 0)		I _{EBO}	-	10	
On Characteristics (1)					
DC Current Gain (I _C = 1.2A, V _{CE} = 5V)		h	30 (typical)	-	-
Collector-Emitter Saturatio ($I_C = 5A$, $I_B = 1mA$) ($I_C = 8A$, $I_B = 2.5mA$)	n Voltage	V _{CE (sat)}	-	1.5 3	V
Base-Emitter Saturation Voltage ($I_C = 5.0A$, $I_B = 1mA$) ($I_C = 8.0A$, $I_B = 2.5mA$)		V _{BE (sat)}	-	1.4 1.8] v
Switching Characteristics		•	•		
Turn On Time	V_{cc} = 250V, I_{C} = 5A	t _{on}	-	0.5	
Storage Time	I _{B1} = 1A, I _{B2} = -2A	t _s	-	3.5	μs
			i		1

(1) Pulse Test : Pulse Width = 300µs, Duty Cycle ≤2%.



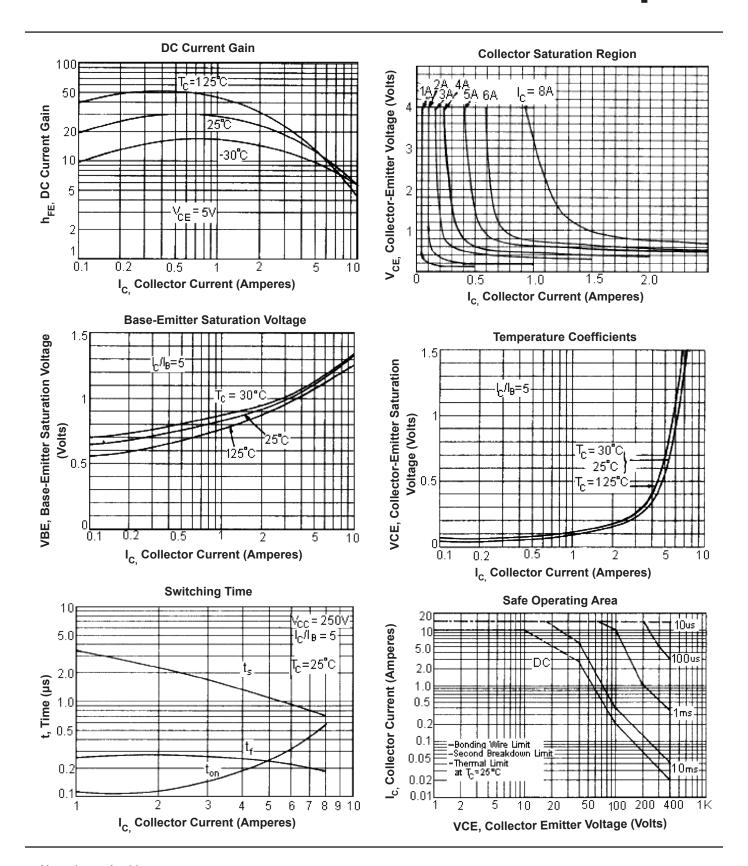
0.5

Fall Time

 t_f

Transistor, NPN TO-3

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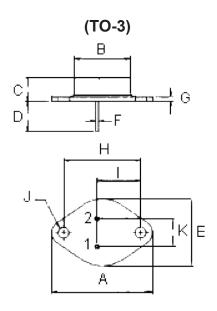
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Dimensions



Dim.	Min.	Max.
А	38.75	39.96
В	19.28	22.23
С	7.96	9.28
D	11.18	12.19
Е	25.2	26.67
F	0.92	1.09
G	1.38	1.62
Н	29.9	30.4
I	16.64	17.3
J	3.88	4.36
K	10.67	11.18

Dimensions: (Millimetres)

Pin Configuration

Pin 1. Base

2. Emitter Collector (Case)

Part Number Table

Description	Part Number	
Transistor, NPN, TO-3	BUX80	

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